



# PMZB600UNE

20 V, N-channel Trench MOSFET

21 July 2014

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small SMD plastic package:  $1.0 \times 0.6 \times 0.37$  mm
- ElectroStatic Discharge (ESD) protection  $> 1$  kV HBM
- Drain-source on-state resistance  $R_{DSon} = 470$  m $\Omega$

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25$ °C	-	-	20	V
$V_{GS}$	gate-source voltage		-8	-	8	V
$I_D$	drain current	$V_{GS} = 4.5$ V; $T_{amb} = 25$ °C	[1]	-	0.6	A
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5$ V; $I_D = 0.6$ A; $T_j = 25$ °C	-	470	620	m $\Omega$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain  $1$  cm<sup>2</sup>.

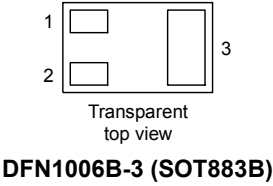
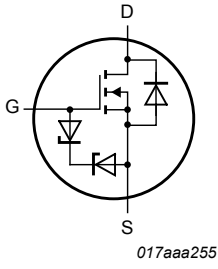


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### 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>Transparent top view DFN1006B-3 (SOT883B)</p>	 <p>017aaa255</p>
2	S	source		
3	D	drain		

### 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMZB600UNE	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

### 7. Marking

Table 4. Marking codes

Type number	Marking code
PMZB600UNE	0101 1000

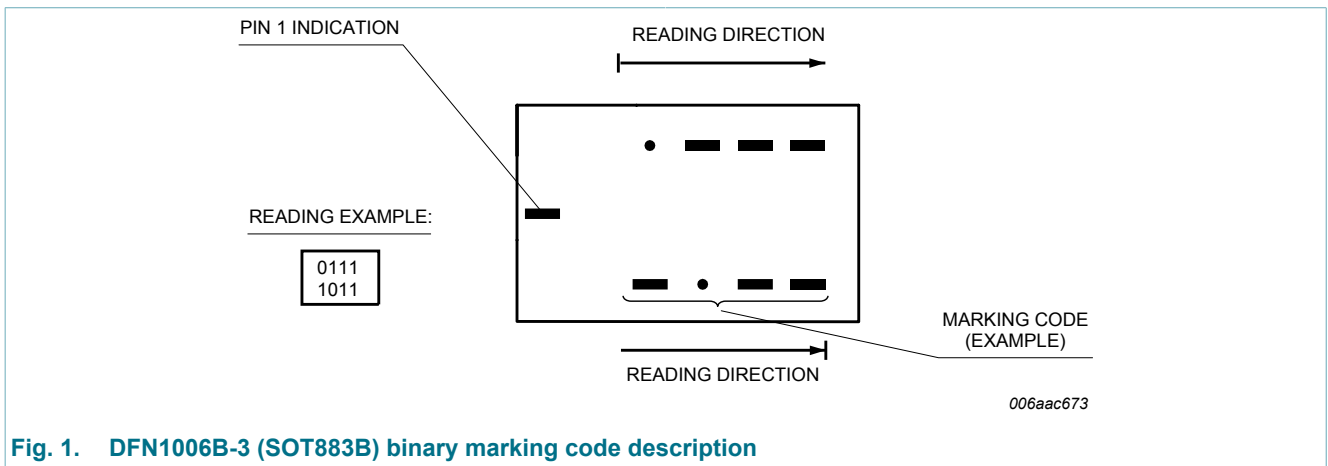


Fig. 1. DFN1006B-3 (SOT883B) binary marking code description

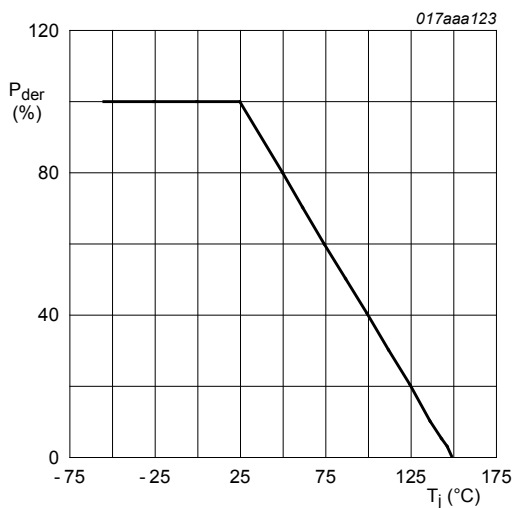
## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

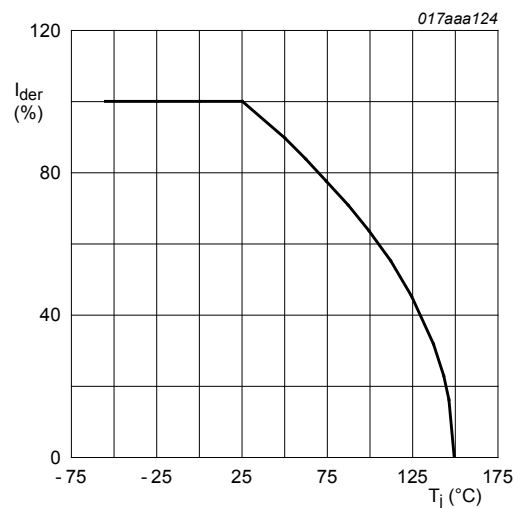
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	0.6	A
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	0.4	A
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	2.5	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T <sub>sp</sub> = 25 °C		-	2700	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
<b>Source-drain diode</b>						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.4	A

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



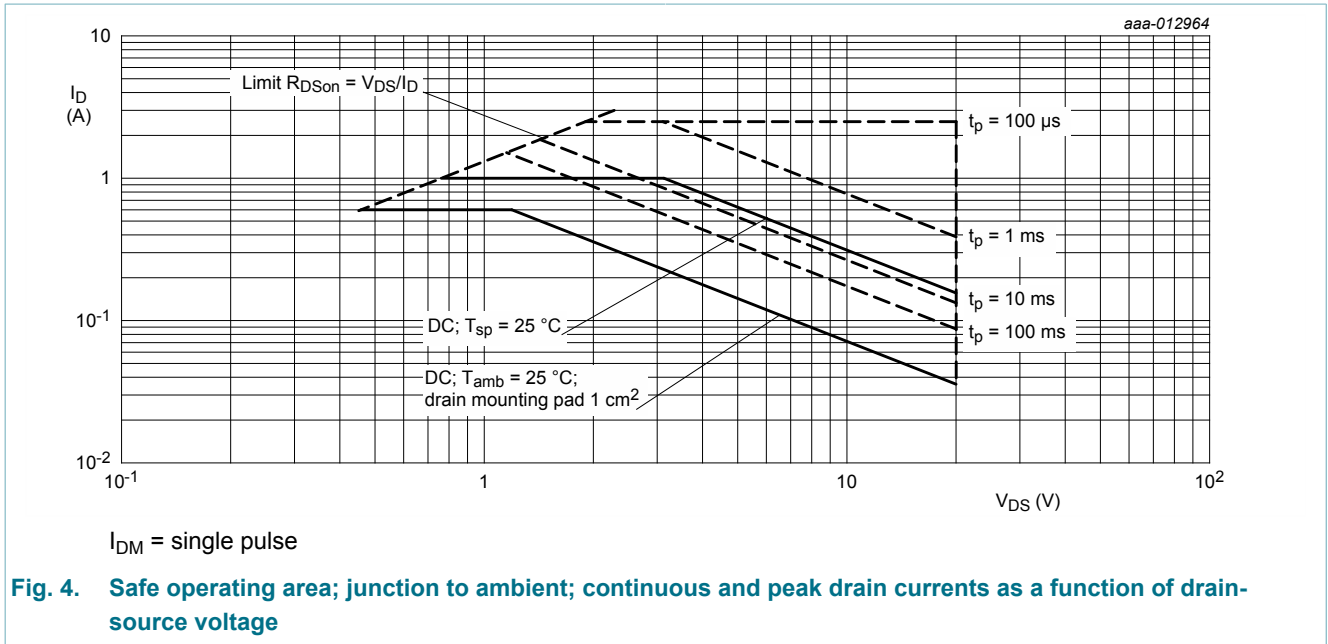
**Fig. 2. Normalized total power dissipation as a function of junction temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$



**Fig. 3. Normalized continuous drain current as a function of junction temperature**

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$



## 9. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	305	360	K/W
			[2]	-	150	175	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	40	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

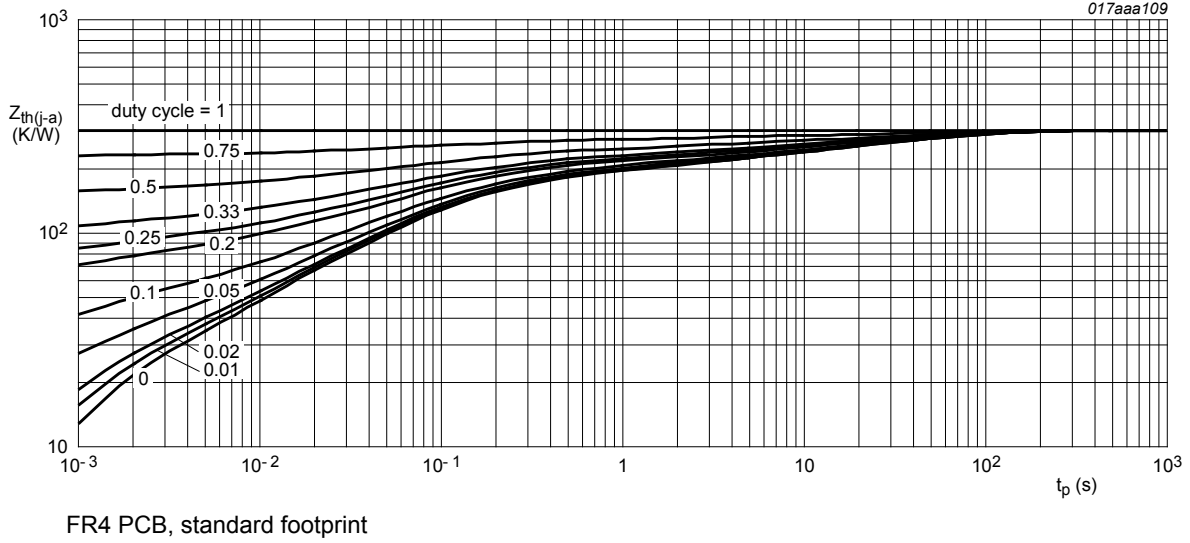


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

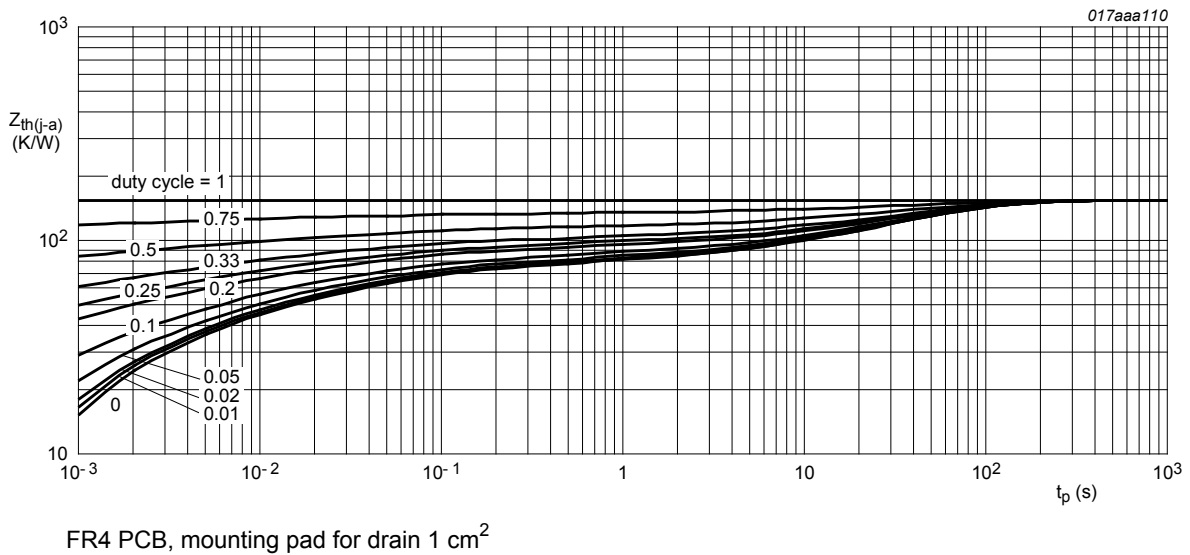


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	0.45	0.7	0.95	V
$I_{DSS}$	drain leakage current	$V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
		$V_{DS} = 20 V; V_{GS} = 0 V; T_j = 150 \text{ }^\circ C$	-	-	10	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 8 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	10	$\mu A$
		$V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-10	$\mu A$
		$V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
		$V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-1	$\mu A$
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 V; I_D = 0.6 A; T_j = 25 \text{ }^\circ C$	-	470	620	m $\Omega$
		$V_{GS} = 4.5 V; I_D = 0.6 A; T_j = 150 \text{ }^\circ C$	-	760	1000	m $\Omega$
		$V_{GS} = 2.5 V; I_D = 0.5 A; T_j = 25 \text{ }^\circ C$	-	620	850	m $\Omega$
		$V_{GS} = 1.8 V; I_D = 0.1 A; T_j = 25 \text{ }^\circ C$	-	845	1300	m $\Omega$
		$V_{GS} = 1.5 V; I_D = 10 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	1125	3000	m $\Omega$
		$V_{GS} = 1.2 V; I_D = 1 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	2210	-	m $\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = 5 V; I_D = 0.6 A; T_j = 25 \text{ }^\circ C$	-	1	-	S
$R_G$	gate resistance	$f = 1 \text{ MHz}$	-	34	-	$\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 10 V; I_D = 0.6 A; V_{GS} = 4.5 V; T_j = 25 \text{ }^\circ C$	-	0.4	0.7	nC
$Q_{GS}$	gate-source charge		-	0.1	-	nC
$Q_{GD}$	gate-drain charge		-	0.1	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 10 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	21.3	-	pF
$C_{oss}$	output capacitance		-	5.4	-	pF
$C_{riss}$	reverse transfer capacitance		-	4.2	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 10 V; I_D = 0.6 A; V_{GS} = 4.5 V; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ }^\circ C$	-	5.6	-	ns
$t_r$	rise time		-	9.2	-	ns
$t_{d(off)}$	turn-off delay time		-	19	-	ns
$t_f$	fall time		-	51	-	ns

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 0.36 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.8	1.2	V

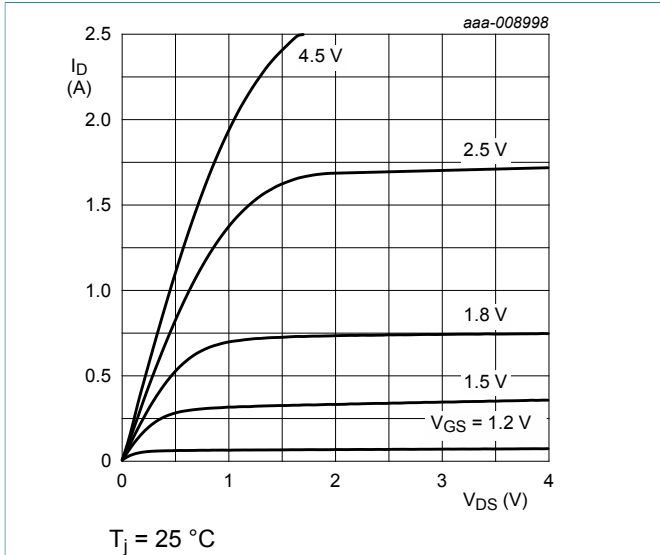


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

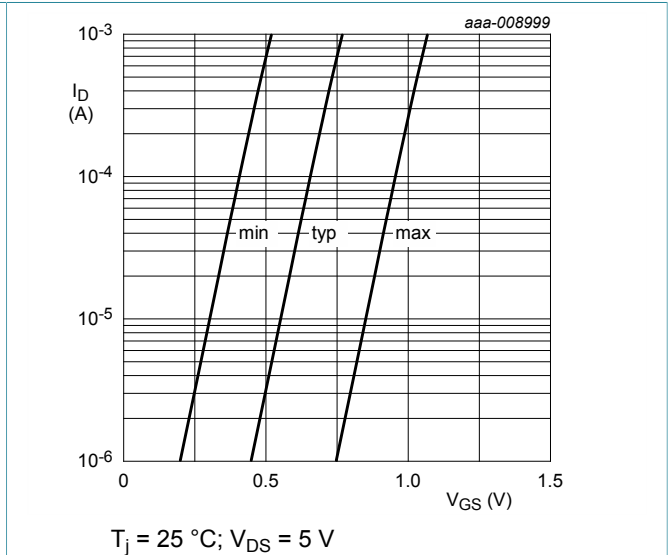


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

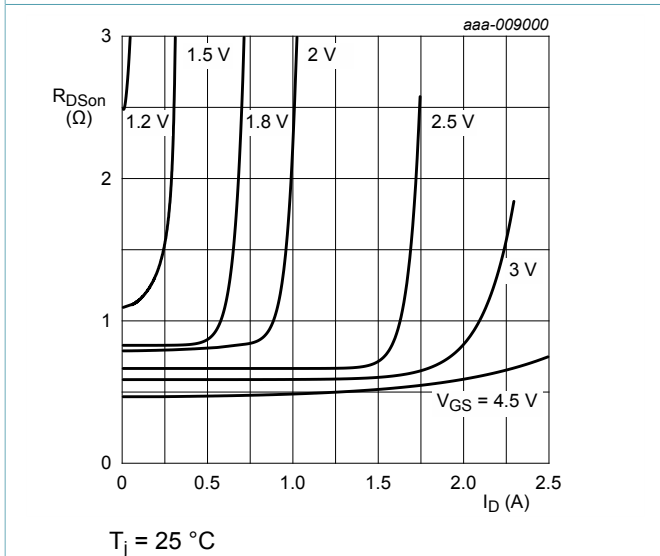


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

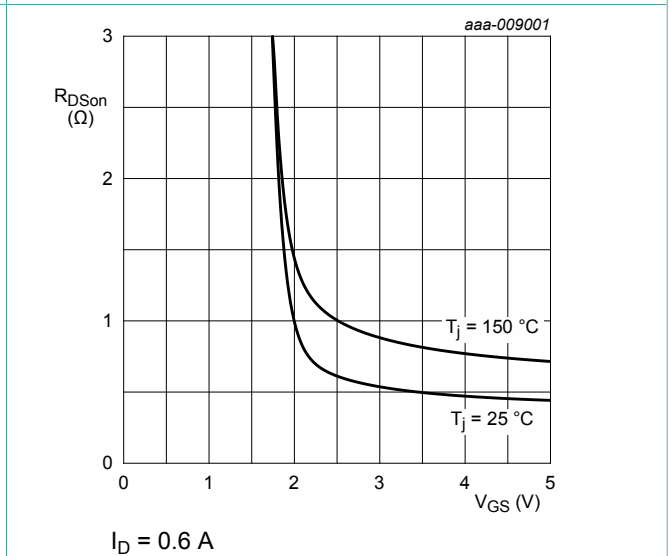
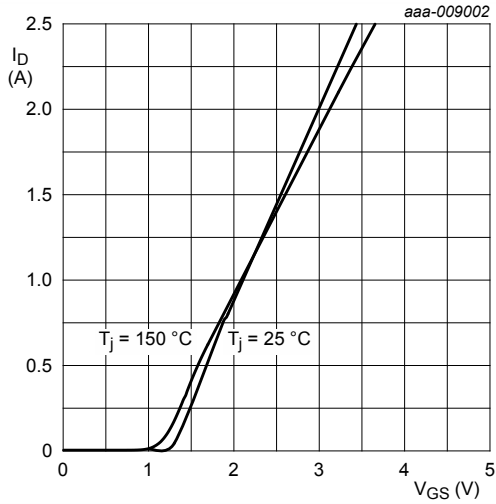


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values



$$V_{DS} > I_D \times R_{DSon}$$

Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

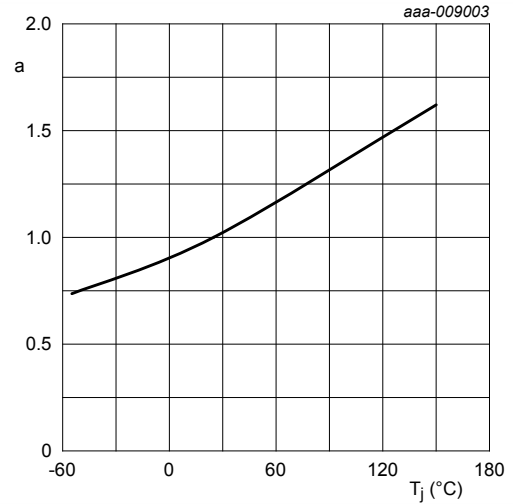
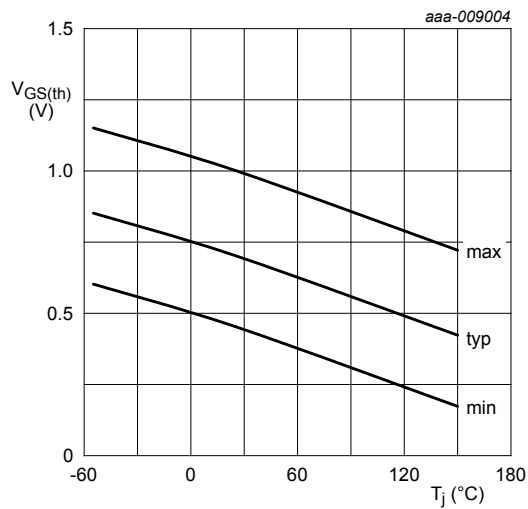


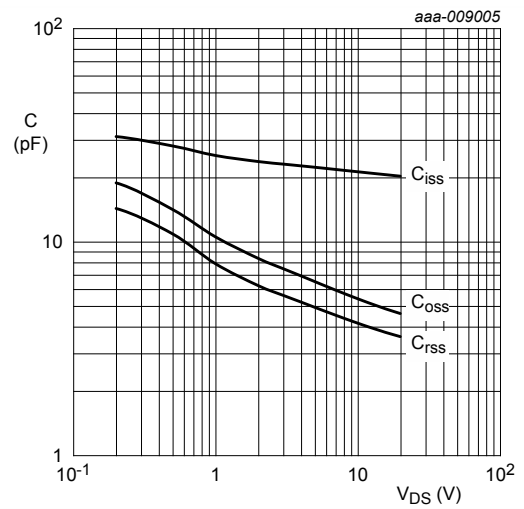
Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



$$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$$

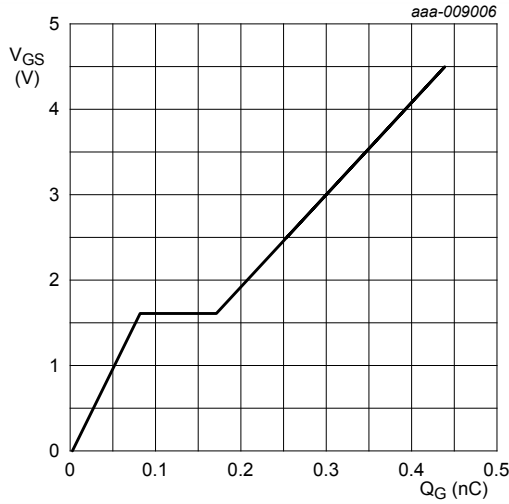
Fig. 13. Gate-source threshold voltage as a function of junction temperature



$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values





$I_D = 0.6 \text{ A}; V_{DS} = 10 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig. 15. Gate-source voltage as a function of gate charge; typical values

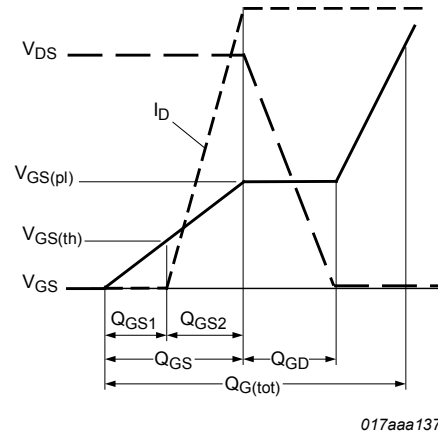
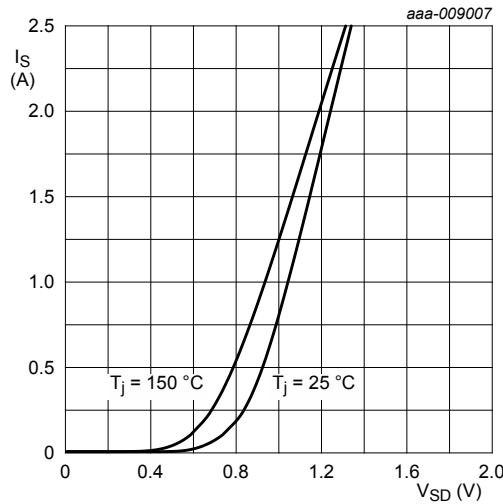


Fig. 16. MOSFET transistor: Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$

Fig. 17. Source current as a function of source-drain voltage; typical values

## 11. Test information

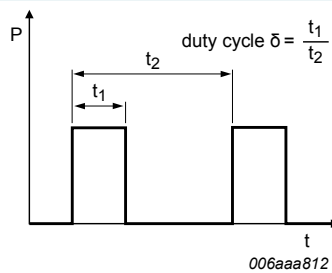


Fig. 18. Duty cycle definition

## 12. Package outline

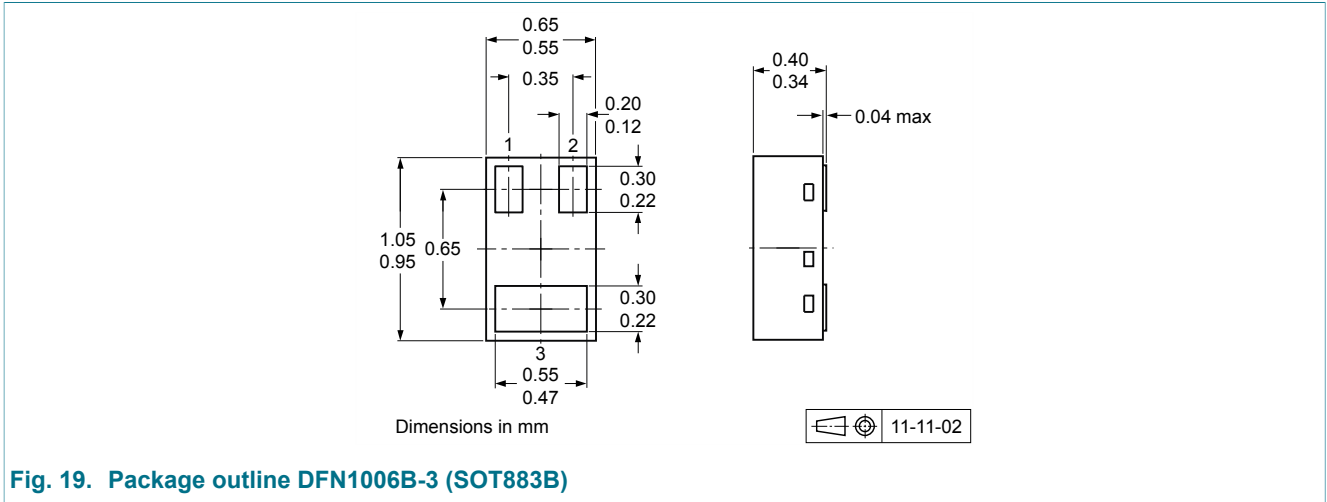


Fig. 19. Package outline DFN1006B-3 (SOT883B)

## 13. Soldering

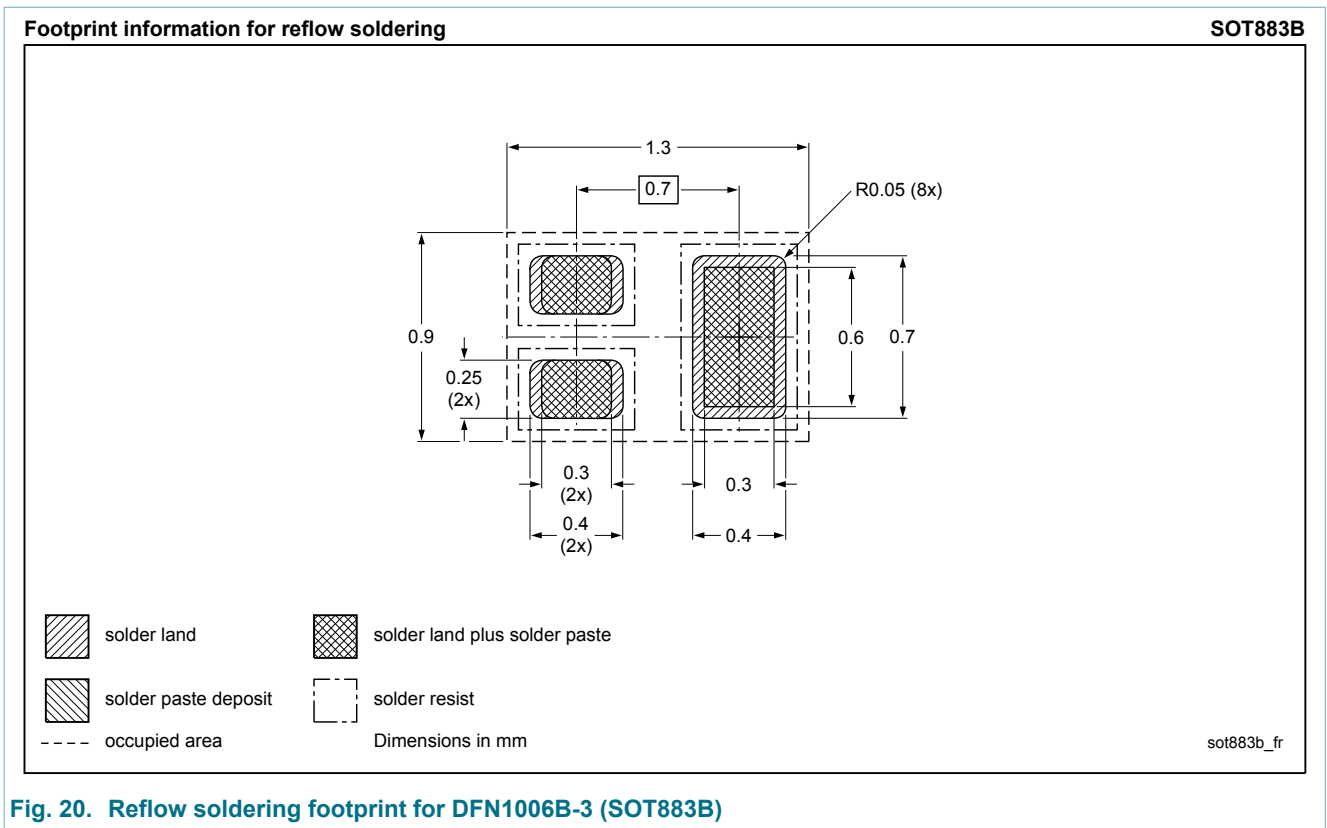


Fig. 20. Reflow soldering footprint for DFN1006B-3 (SOT883B)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZB600UNE v.1	20140721	Product data sheet	-	-

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Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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